

APPENDIX

10. The claims on appeal for U.S. Application Serial No. 09/516,615, filed March 1, 2000

24. A poly-poly capacitor comprising planar upper and lower plate electrodes, wherein at least the planar upper plate electrode is composed of SiGe polysilicon, said plate electrodes being separated by an insulator structure and said planar upper plate electrode is located directly above said insulator structure and said lower plate electrode is located directly below said insulator structure.

25. The poly-poly capacitor of Claim 24 wherein the lower plate electrode is composed of polysilicon.

26. A poly-poly capacitor comprising planar upper and lower plate electrodes, wherein the planar upper plate electrode and the lower plate electrode are both composed of SiGe polysilicon, said plate electrodes being separated by an insulator structure.

27. The poly-poly capacitor of Claim 24 wherein at least one said plate electrodes is polysilicon from a FET gate or a bipolar emitter.

28. The poly-poly capacitor of Claim 24 further including a bipolar device region and a FET region, wherein said capacitor, bipolar device region and FET region are electrically isolated from each by isolation regions.

29. A semiconductor device, comprising:

a capacitor having first and second plate electrodes, one of said plate electrodes being comprised of a first conductive patterned layer; and

a bipolar device having first and second electrodes, one of said electrodes being comprised of said conductive patterned layer;

wherein said first conductive patterned layer is comprised of SiGe material.

30. A semiconductor structure, comprising

a first layer of polysilicon patterned to form a first electrode of a MOS device and a first plate electrode of a capacitor, and

a second layer of polysilicon patterned to form a first electrode of a bipolar device and a second plate electrode of said capacitor, said second layer being comprised of SiGe polysilicon.